

Amendments to the Specification

Please amend the paragraph at page 12, lines 10-25 in the following manner:

According to another embodiment of the present invention, a semiconductor device is provided that includes a divider resistor circuit that is configured to obtain a voltage output through voltage division and adjust the voltage output through cutting one or more fuse elements. The divider resistor circuit according to one embodiment includes plural resistance value adjusting resistor elements ~~the~~ that are serially connected, plural fuse MOS transistors as the fuse elements that are connected in parallel to the resistance value adjusting resistor elements, the nonvolatile memory cell according to one embodiment of the present invention, and a read circuit for switching on/off the fuse MOS transistors according to the storage state of the nonvolatile memory cell, wherein at least one of the fuse MOS transistors and the read circuit is configured as the peripheral circuit transistor according to one embodiment of the present invention.

Please amend the paragraph bridging page 15 and 16, in the following manner:

According to another embodiment of the present invention, a semiconductor device is provided that includes a divider resistor circuit that is configured to obtain a voltage output through voltage division and adjust the voltage output through cutting one or more fuse elements. The divider resistor circuit according to one embodiment includes plural resistance value adjusting resistor elements ~~the~~ that are serially connected, plural fuse MOS transistors as the fuse elements that are connected in parallel to the resistance value adjusting resistor elements, the nonvolatile memory cell according to one embodiment of the present invention, and a read circuit for switching on/off the fuse MOS transistors according to the storage state of the nonvolatile memory cell, wherein at least one of the fuse MOS transistors and the read

circuit is configured as the peripheral circuit transistor according to one embodiment of the present invention.

Please amend the paragraph bridging pages 129-130 in the following manner:

According to another aspect of the present invention, in a semiconductor device that includes a divider resistor circuit that is configured to obtain a voltage output through voltage division and adjust the voltage output through cutting one or more fuse elements, by configuring the divider resistor circuit to include plural resistance value adjusting resistor elements ~~the~~ that are serially connected, plural fuse MOS transistors as the fuse elements that are connected in parallel to the resistance value adjusting resistor elements, the nonvolatile memory cell according to one embodiment of the present invention, and a read circuit for switching on/off the fuse MOS transistors according to the storage state of the nonvolatile memory cell, and by configuring at least one of the fuse MOS transistors and the read circuit into the peripheral circuit transistor according to one embodiment of the present invention, the output voltage of the divider resistor circuit may be adjusted according to the storage state of the nonvolatile memory cell having good writing characteristics. Further, by changing the storage state of the nonvolatile memory cell, the output voltage of the divider resistor circuit may be reset, for example.

Please amend the paragraph bridging pages 137-138 in the following manner:

According to another aspect of the present invention, in a semiconductor device that includes a divider resistor circuit that is configured to obtain a voltage output through voltage division and adjust the voltage output through cutting one or more fuse elements, by

configuring the divider resistor circuit to include plural resistance value adjusting resistor elements ~~the~~ that are serially connected, plural fuse MOS transistors as the fuse elements that are connected in parallel to the resistance value adjusting resistor elements, the nonvolatile memory cell according to one embodiment of the present invention, and a read circuit for switching on/off the fuse MOS transistors according to the storage state of the nonvolatile memory cell, and by configuring at least one of the fuse MOS transistors and the read circuit into the peripheral circuit transistor according to one embodiment of the present invention, the output voltage of the divider resistor circuit may be adjusted according to the storage state of the nonvolatile memory cell having good writing characteristics. Further, by changing the storage state of the nonvolatile memory cell, the output voltage of the divider resistor circuit may be reset, for example.